

## General Description

The WSP6956 is the highest performance trench Dual N-ch MOSFET with extreme high cell density, which provide excellent  $R_{DS(on)}$  and gate charge for most of the synchronous buck converter applications.

## Features

- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

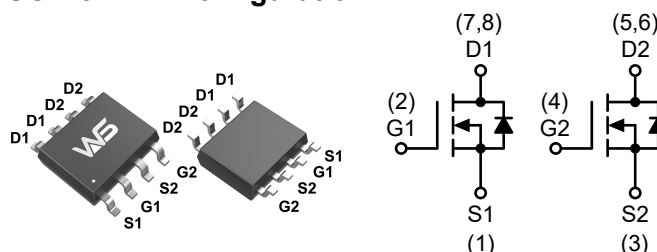
## Product Summary

$BV_{DSS}$	$R_{DS(on)}$	$I_D$
60V	15m $\Omega$	10A

## Applications

- SMPS Synchronous Rectification.
- DC-DC Conversion.
- Load Switch.

## SOP-8L Pin Configuration



## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b>			
$V_{DSS}$	Drain-Source Voltage	60	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	
$I_S$	Diode Continuous Forward Current	$T_A=25^\circ\text{C}$	A
$I_D$	Continuous Drain Current	$T_A=25^\circ\text{C}$	
		$T_A=70^\circ\text{C}$	
$I_{DM}^a$	Pulsed Drain Current	$T_A=25^\circ\text{C}$	38
$P_D$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	3.5
		$T_A=70^\circ\text{C}$	2.2
$R_{\theta JA}^c$	Thermal Resistance-Junction to Ambient	$t \leq 10s$	35
		Steady State	70
$I_{AS}^b$	Avalanche Current, Single pulse	$L=0.1mH$	27
$E_{AS}^b$	Avalanche Energy, Single pulse	$L=0.1mH$	36

Note a : Pulse width limited by max. junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature  $150^\circ\text{C}$  (initial temperature  $T_J=25^\circ\text{C}$ ).

Note c : Surface Mounted on  $1in^2$  pad area.

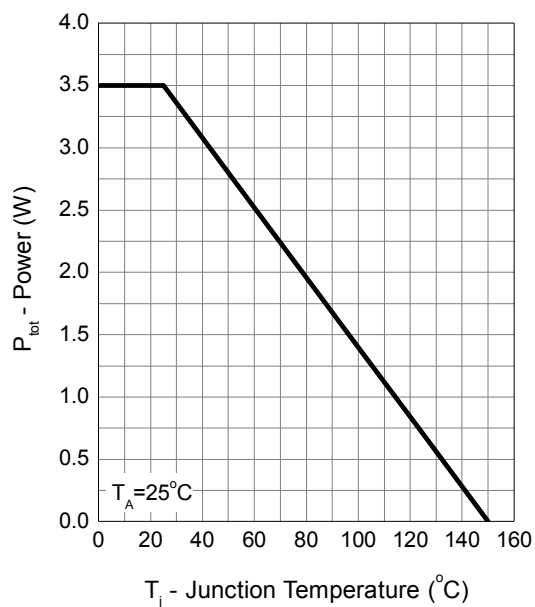
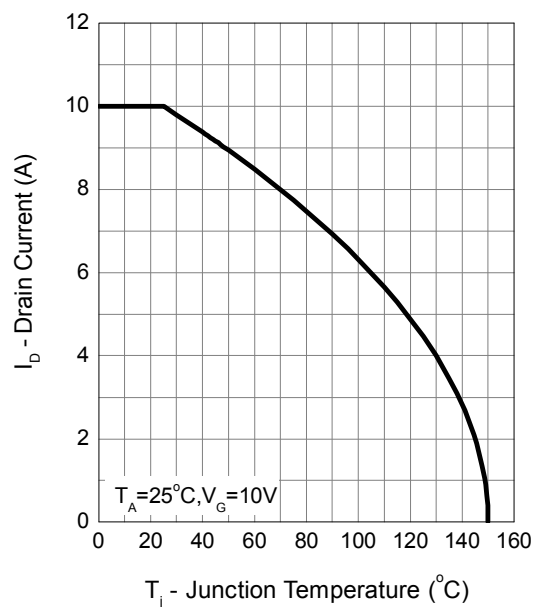
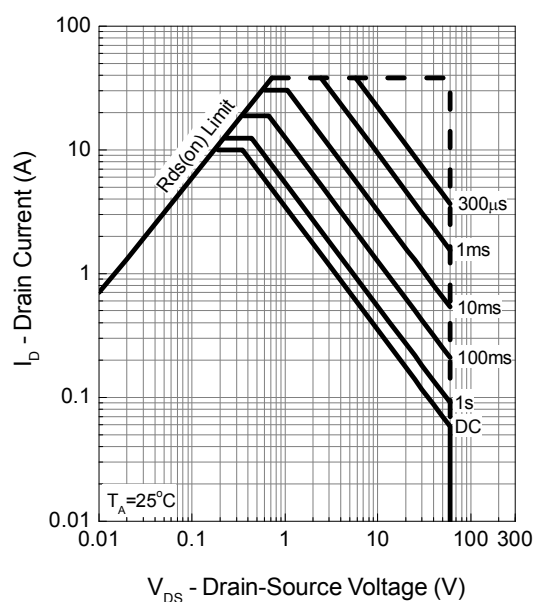
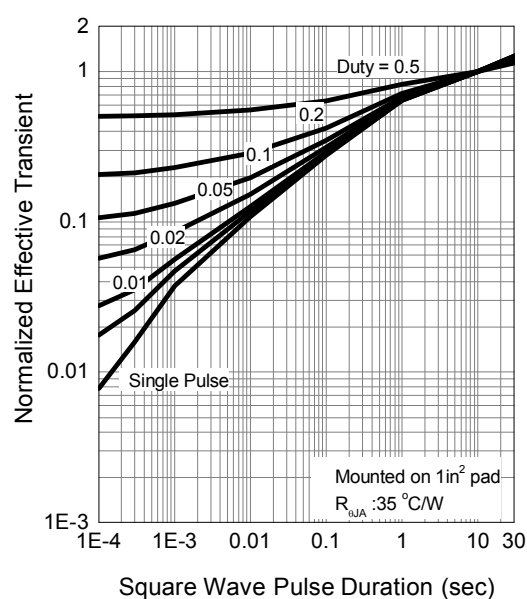
## Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA	60	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	1	μA
		T <sub>J</sub> =85°C	-	-	30	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250μA	1	1.5	2.5	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
R <sub>DS(ON)</sub> <sup>d</sup>	Drain-Source On-state Resistance	V <sub>GS</sub> =10V, I <sub>DS</sub> =10A	-	15	20	mΩ
		V <sub>GS</sub> =4.5V, I <sub>DS</sub> =9A	-	18	24	
Diode Characteristics						
V <sub>SD</sub> <sup>d</sup>	Diode Forward Voltage	I <sub>SD</sub> =10A, V <sub>GS</sub> =0V	-	0.8	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>SD</sub> =10A, dl <sub>SD</sub> /dt=100A/μs	-	21	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	22	-	nC
Dynamic Characteristics <sup>e</sup>						
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	-	2.5	-	Ω
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, Frequency=1.0MHz	-	1370	1780	pF
C <sub>oss</sub>	Output Capacitance		-	135	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	60	-	
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>DD</sub> =30V, R <sub>L</sub> =30Ω, I <sub>DS</sub> =1A, V <sub>GEN</sub> =10V, R <sub>G</sub> =6Ω	-	8	15	ns
t <sub>r</sub>	Turn-on Rise Time		-	14	26	
t <sub>d(OFF)</sub>	Turn-off Delay Time		-	12	22	
t <sub>f</sub>	Turn-off Fall Time		-	38	69	
Gate Charge Characteristics <sup>e</sup>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =30V, V <sub>GS</sub> =4.5V, I <sub>DS</sub> =10A	-	12	-	nC
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>DS</sub> =10A	-	26	37	
Q <sub>gs</sub>	Gate-Source Charge		-	5	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	5	-	

Note d : Pulse test ; pulse width≤300μs, duty cycle≤2%.

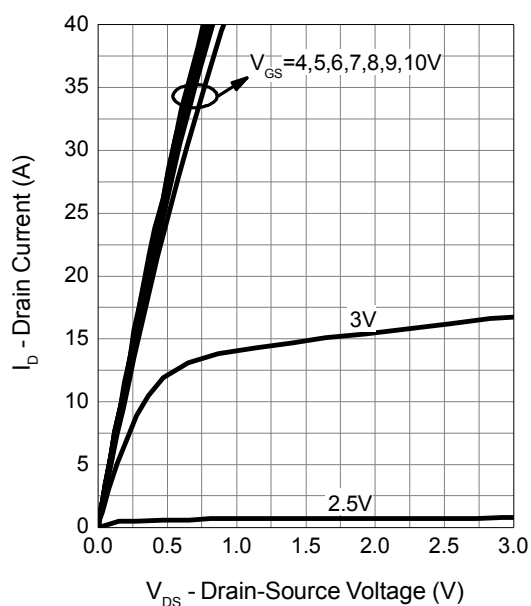
Note e : Guaranteed by design, not subject to production testing.

## Typical Operating Characteristics

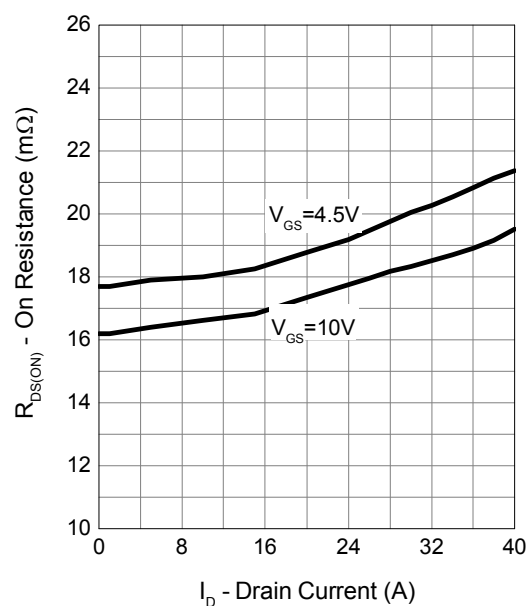
**Power Dissipation**

**Drain Current**

**Safe Operation Area**

**Thermal Transient Impedance**


## Typical Operating Characteristics (Cont.)

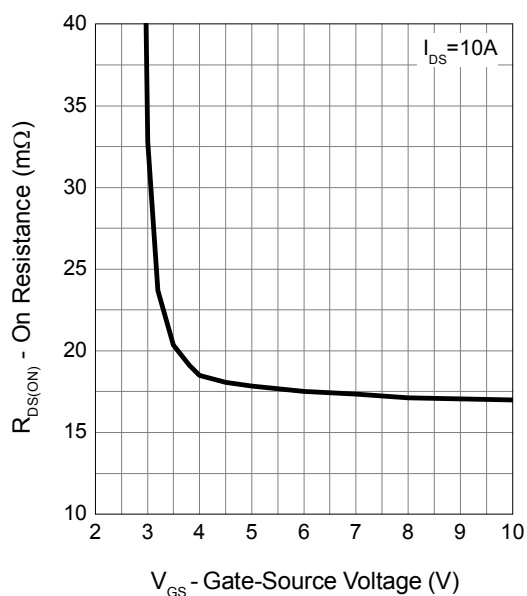
**Output Characteristics**



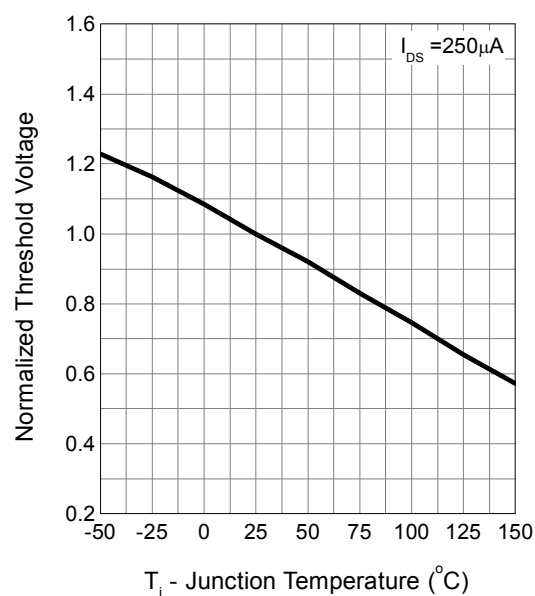
**Drain-Source On Resistance**



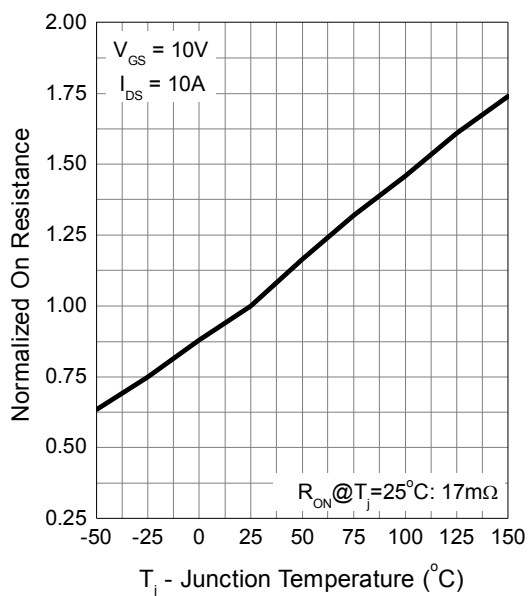
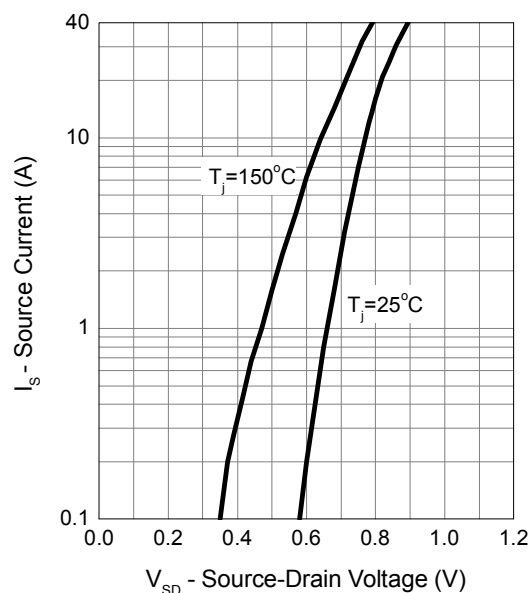
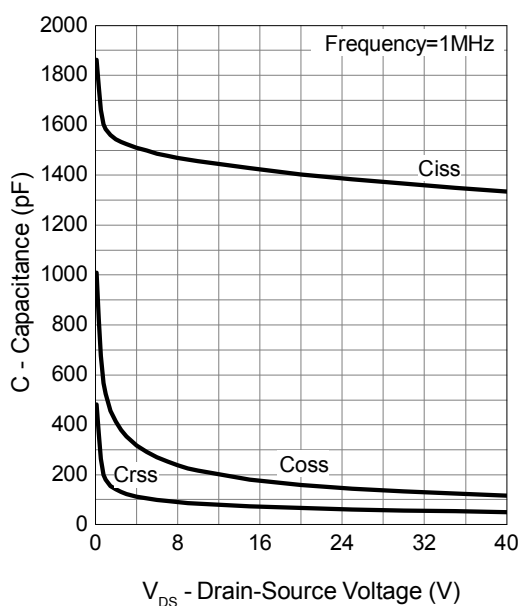
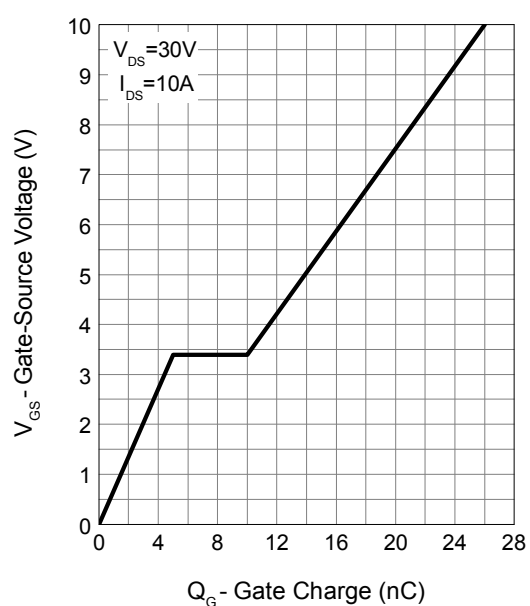
**Gate-Source On Resistance**



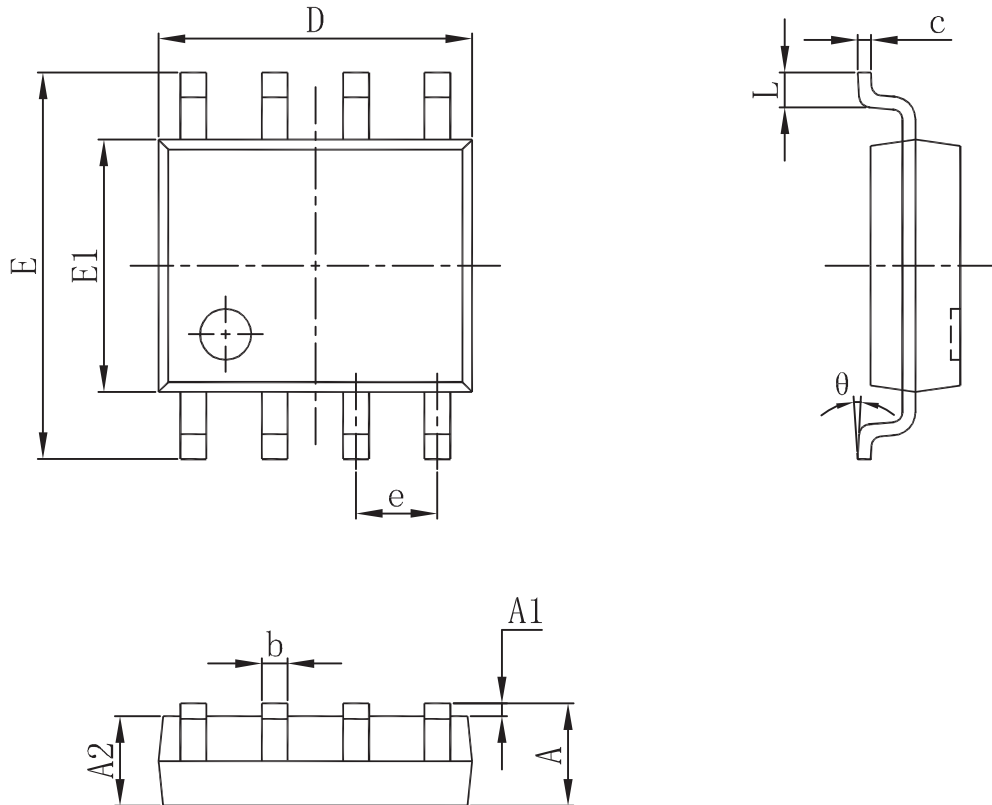
**Gate Threshold Voltage**



## Typical Operating Characteristics (Cont.)

**Drain-Source On Resistance**

**Source-Drain Diode Forward**

**Capacitance**

**Gate Charge**


## Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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